

RoHS Compliant Product

## Description

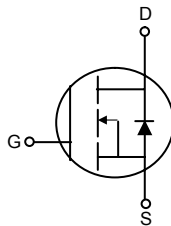
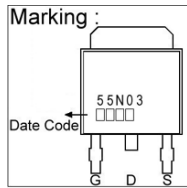
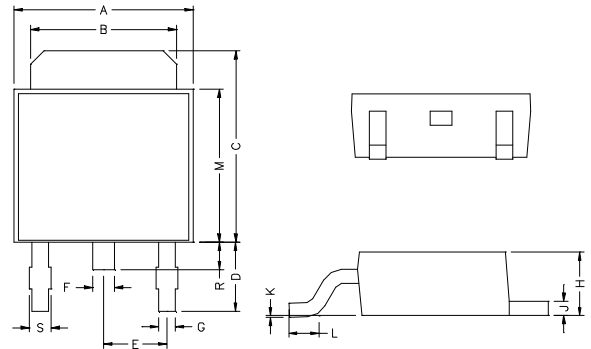
The SSD55N03 provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-252 is universally preferred for all commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters.

## Features

- \* Repetitive Avalanche Rated
- \* Dynamic dv/dt Rating
- \* Simple Drive Requirement
- \* Fast Switching

TO-252



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.40	6.80	G	0.50	0.70
B	5.20	5.50	H	2.20	2.40
C	6.80	7.20	J	0.45	0.55
D	2.20	2.80	K	0	0.15
E	2.30 REF.		L	0.90	1.50
F	0.70	0.90	M	5.40	5.80
S	0.60	0.90	R	0.80	1.20

## Absolute Maximum Ratings

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V <sub>DS</sub>	25	V
Gate-Source Voltage	V <sub>GS</sub>	± 20	V
Continuous Drain Current, V <sub>GS</sub> @10V	I <sub>D</sub> @T <sub>C</sub> =25°C	55	A
Continuous Drain Current, V <sub>GS</sub> @10V	I <sub>D</sub> @T <sub>C</sub> =100°C	35	A
Pulsed Drain Current <sup>1</sup>	I <sub>DM</sub>	215	A
Total Power Dissipation	P <sub>D</sub> @T <sub>C</sub> =25°C	62.5	W
Linear Derating Factor		0.5	W/°C
Single Pulse Avalanche Energy <sup>2</sup>	E <sub>AS</sub>	240	mJ
Avalanche Current	I <sub>AR</sub>	31	A
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55~+150	°C

## Thermal Data

Parameter	Symbol	Ratings	Unit
Thermal Resistance Junction-case	R <sub>thj-c</sub>	2.0	°C/W
Thermal Resistance Junction-ambient	R <sub>thj-a</sub>	110	°C/W

## Electrical Characteristics( T<sub>j</sub>=25°C Unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	25	-	-	V	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA
Breakdown Voltage Temp. Coefficient	ΔBV <sub>DSS</sub> /ΔT <sub>j</sub>	-	0.037	-	V/°C	Reference to 25°C, I <sub>D</sub> =1mA
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.0	-	3.0	V	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA
Gate-Source Leakage Current	I <sub>GSS</sub>	-	-	±100	nA	V <sub>GS</sub> =±20V
Drain-Source Leakage Current (T <sub>j</sub> =25°C)	I <sub>DSS</sub>	-	-	1	uA	V <sub>DS</sub> =25V, V <sub>GS</sub> =0
Drain-Source Leakage Current(T <sub>j</sub> =150°C)		-	-	25	uA	V <sub>DS</sub> =20V, V <sub>GS</sub> =0
Static Drain-Source On-Resistance <sup>3</sup>	R <sub>DS(ON)</sub>	-	4.5	6	mΩ	V <sub>GS</sub> =10V, I <sub>D</sub> =30A
		-	7	9		V <sub>GS</sub> =4.5V, I <sub>D</sub> =30A
Total Gate Charge <sup>3</sup>	Q <sub>g</sub>	-	16.8	-	nC	I <sub>D</sub> =28A V <sub>DS</sub> =20V V <sub>GS</sub> =5V
Gate-Source Charge	Q <sub>gs</sub>	-	6	-		
Gate-Drain ("Miller") Charge	Q <sub>gd</sub>	-	4.9	-		
Turn-on Delay Time <sup>3</sup>	T <sub>d(ON)</sub>	-	15.1	-	nS	V <sub>DD</sub> =15V I <sub>D</sub> =28A V <sub>GS</sub> =10V R <sub>G</sub> =3.3Ω R <sub>D</sub> =0.53Ω
Rise Time	T <sub>r</sub>	-	4	-		
Turn-off Delay Time	T <sub>d(OFF)</sub>	-	45.2	-		
Fall Time	T <sub>f</sub>	-	7.6	-		
Input Capacitance	C <sub>iss</sub>	-	2326	-	pF	V <sub>GS</sub> =0V V <sub>DS</sub> =25V f=1.0MHz
Output Capacitance	C <sub>oss</sub>	-	331	-		
Reverse Transfer Capacitance	C <sub>rss</sub>	-	174	-		
Forward Transconductance	G <sub>fs</sub>	-	30	-	S	V <sub>DS</sub> =10V, I <sub>D</sub> =28A

## Source-Drain Diode

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Forward On Voltage <sup>3</sup>	V <sub>SD</sub>	-	-	1.5	V	I <sub>S</sub> =20 A, V <sub>GS</sub> =0V, T <sub>j</sub> =25°C
Continuous Source Current(Body Diode)	I <sub>S</sub>	-	-	55	A	V <sub>D</sub> =V <sub>G</sub> =0V, V <sub>S</sub> =1.5 V

Notes: 1.Pulse width limited by safe operating area.

2.Staring T<sub>j</sub>=25°C, V<sub>DD</sub>=25V, L=0.1mH, R<sub>G</sub>=25 Ω, I<sub>AS</sub>=10A

3.Pulse width ≤300us, dutycycle≤2%.

## Characteristics Curve

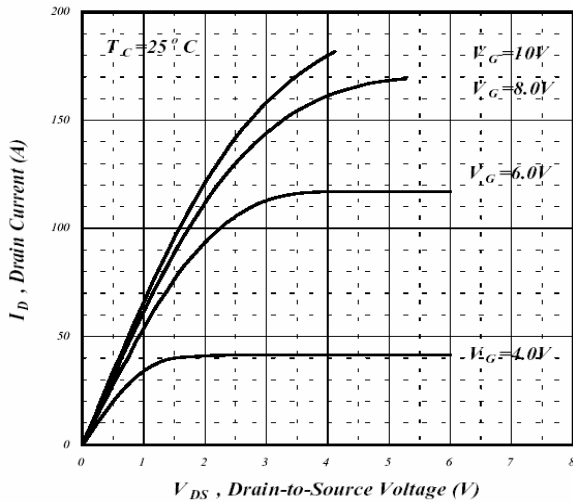


Fig 1. Typical Output Characteristics

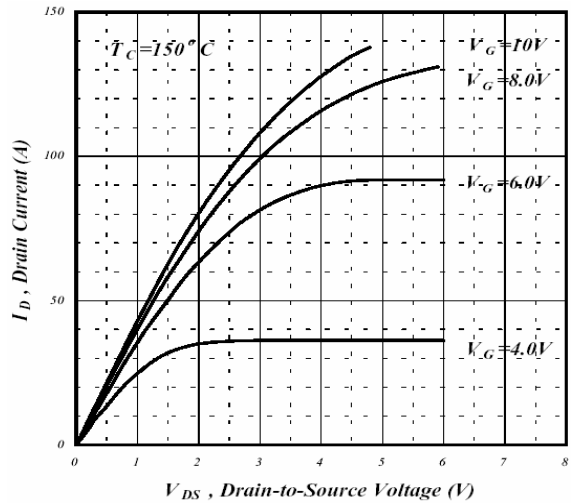


Fig 2. Typical Output Characteristics

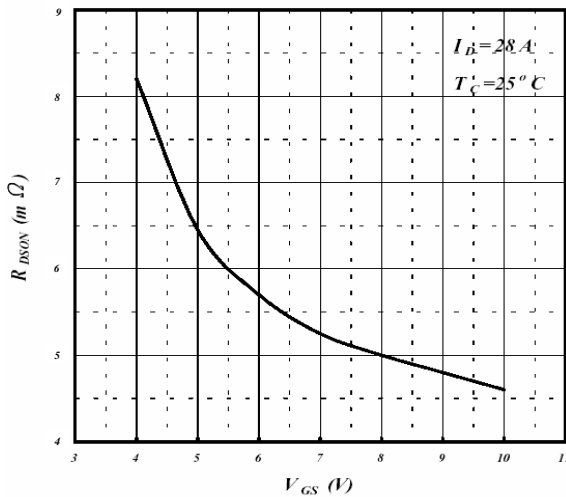


Fig 3. On-Resistance v.s. Gate Voltage

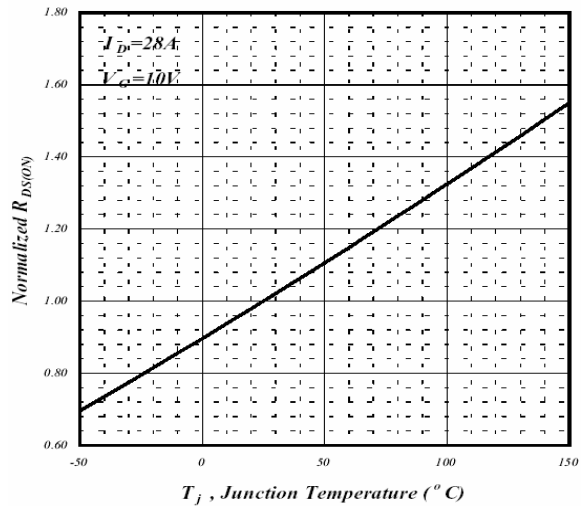


Fig 4. Normalized On-Resistance v.s. Junction Temperature

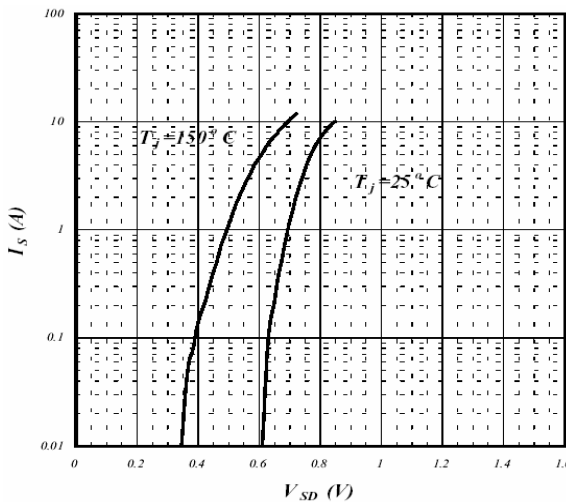


Fig 5. Forward Characteristics of Reverse Diode

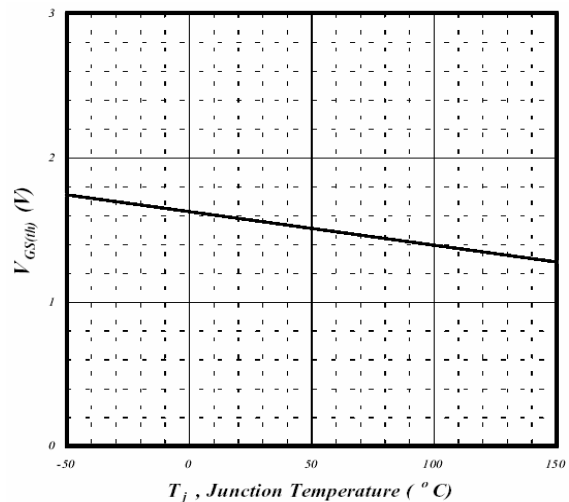


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

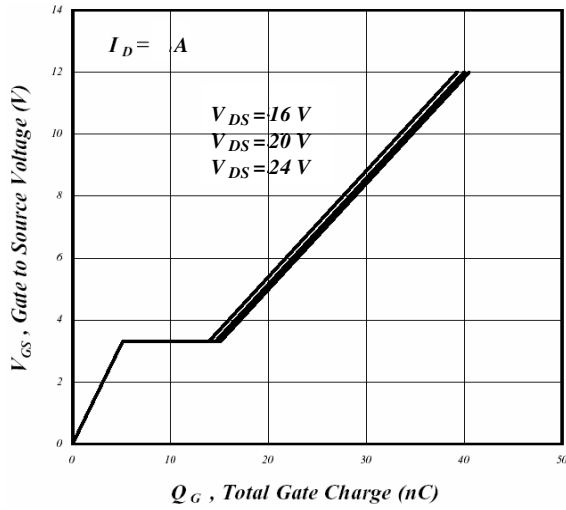


Fig 7. Gate Charge Characteristics

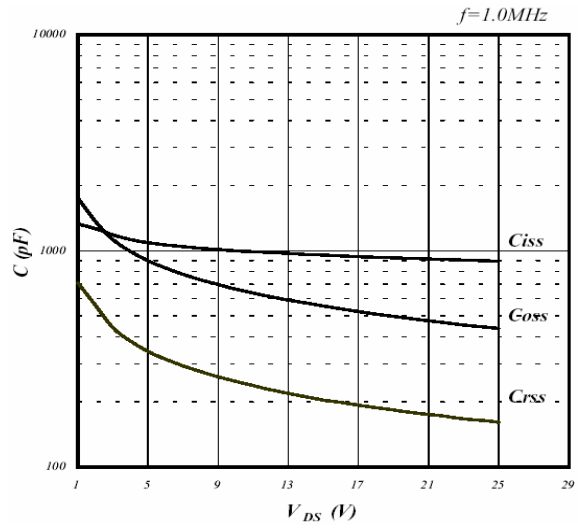


Fig 8. Typical Capacitance Characteristics

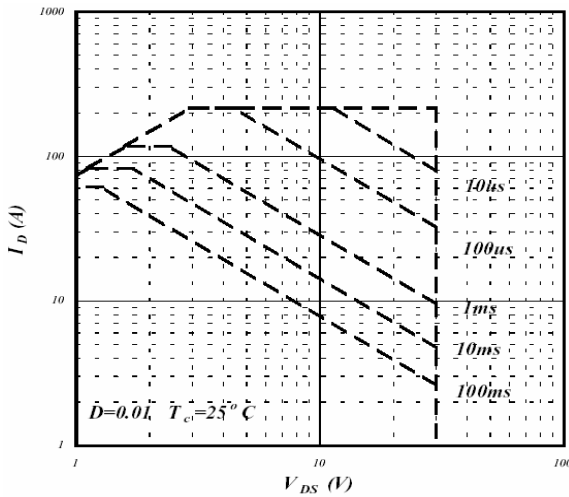


Fig 9. Maximum Safe Operating Area

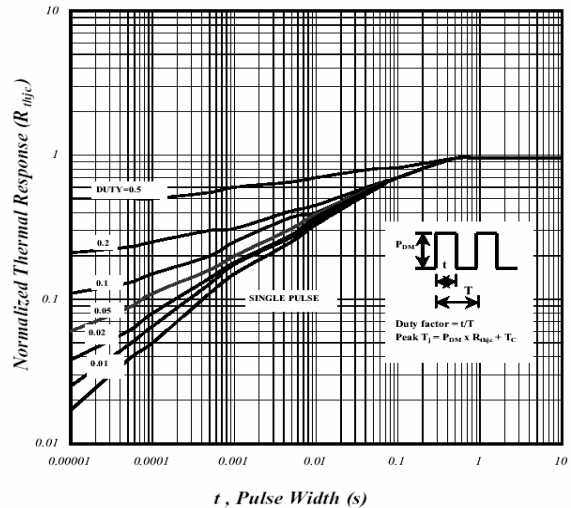


Fig 10. Effective Transient Thermal Impedance

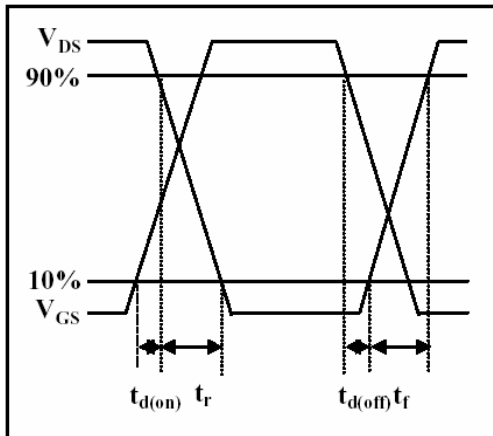


Fig 11. Switching Time Waveform

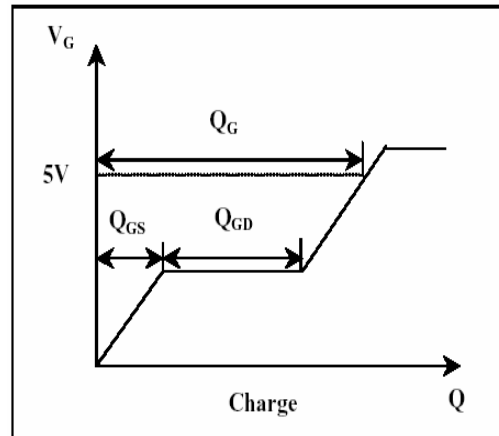


Fig 12. Gate Charge Waveform